

IN THE CLAIMS:

1. (Original) An intermediate base for a module having at least one semiconductor component, said base comprising a flat base body having an upper face on which internal connections are formed for connection to connecting elements of a semiconductor component, a lower face which is provided with external connections for making contact with a circuit carrier, and through-holes between the upper face and the lower face, said through-holes having walls which are at least partially metallized to make a conductive connection between an internal connection on the upper face and a corresponding external connection on the lower face, the walls of the through-holes being at least partially exposed in the region of the lower face of the base body by means of annular notches which are incorporated adjacent to a circumferential edge of the through-holes to form freestanding studs as external connections.

2. (Previously Amended) The intermediate base according to claim 1, wherein annular notches are concentric to form tubular studs.

3. (Previously Amended) The intermediate base according to claim 1, wherein at least one of the notches is eccentric so that the stud associated therewith is approximately in the form of a tubular segment.

4. (Previously Amended) The intermediate base according to claim 1, wherein the base body is a film composed of a plastic material whose coefficient of expansion is approximately the same as the coefficient of expansion of the semiconductor component.

5. (Previously Amended) The intermediate base according to claim 4, wherein the film is composed of liquid crystal polymer.

6. (Previously Amended) The intermediate base according to claim 1, wherein the external connections are in the form of metal layers on an outer rim of the studs.

7. (Previously Amended) The intermediate base according to claim 6, wherein the external connecting elements have an additional solder layer.

8. (Previously Amended) The intermediate base according to claim 6, wherein the through-holes are at least partially filled with a solder material.

9. (Previously Amended) The intermediate base according to claim 1, wherein the internal connections on the upper face of the base body are formed by a metal layer on the component connecting elements of a semiconductor component which is connected to the upper face, with a metal layer continuously covering both the walls of the through-hole and the contact surface of the component connecting element which faces the through-hole.

10. (Original) A semiconductor module comprising a semiconductor chip and an intermediate base, said intermediate base having a flat base body having an upper face on which internal connections are formed for connection to connecting elements of the semiconductor chip, said flat base body having a lower face which is provided with external connections for making contact with a circuit carrier, and through-holes extending between the upper face and the lower face, said through-holes having walls which are at least partially metallized for making a conductive connection between an internal connection on the upper face and a corresponding external connection on the lower face, the walls of each of the through-holes being at least partially exposed in the region of the lower face of the base body by means of annular notches which are incorporated adjacent a circumferential edge of the through-hole to form a freestanding stud as an external connection.

Claims 11-15 (cancelled).

Please add the following new claims:

16. (New) A semiconductor module comprising a semiconductor component and an intermediate base, said intermediate base having a flat base body in the form of a film composed of a plastic material having a coefficient of expansion approximately the same as a coefficient of expansion of the semiconductor component, said base body having an upper face on which internal connections are formed for connection to connecting elements of the semiconductor component, the semiconductor component being connected directly with the upper face of the base body so that the connecting elements rest directly on the internal connections, said flat base body having a lower face which is provided with external

connections for making contact with a circuit carrier, said base body having through-holes extending in each case directly between one of the internal connections on the upper face and an external connection on the lower face, said through-holes having walls which are at least partially metallized for making a conductive connection between an internal connection on the upper face and a corresponding external connection on the lower face and the walls of each of the through-holes being at least partially exposed in the region of the lower face of the base body by means of annular notches which are incorporated adjacent a circumferential edge of the through-hole to form a free-standing stud as an external connection.

17. (New) A semiconductor module according to claim 16, wherein the base body is connected to the semiconductor component via an adhesive layer.

18. (New) A semiconductor module according to claim 16, wherein the annular notches are concentric to form tubular studs.

19. (New) A semiconductor module according to claim 16, wherein at least one of the notches is eccentric so that the stud associated therewith is approximately in the form of a tubular segment.

20. (New) A semiconductor module according to claim 16, wherein the film is composed of a liquid crystal polymer.

21. (New) A semiconductor module according to claim 16, wherein the external connections are in the form of metal layers on an outer rim of the studs.

22. (New) A semiconductor module according to claim 21, wherein the external connections have an additional solder layer.

23. (New) A semiconductor module according to claim 16, wherein the through-holes are at least partially filled with a solder material.

24. (New) A semiconductor module according to claim 16, wherein the internal connections on the upper face of the base body are formed by a metal layer on the connecting elements of the semiconductor component which is connected to the upper

surface, with the metal layer continuously covering both the walls of the through-hole and the contact surface of the component connecting element which faces the through-hole.

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